Product data sheet

1. General description

Low V_{CEsat} PNP transistor and NPN resistor-equipped transistor encapsulated a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low V_{CEsat} (BISS) transistor and resistor-equipped transistor in one package
- Low 'threshold' voltage (< 1 V) compared to MOSFET
- · Low drive power required
- · Space-saving solution
- · Reduction of component count
- AEC-Q101 qualified

3. Applications

- · Supply line switches
- Battery charger switches
- · High-side switches for LEDs, drivers and backlights
- · Portable equipment

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1: PNP I	ow V _{CEsat} transistor					
V_{CEO}	collector-emitter voltage	open base	-	-	-15	V
I _C	collector current		-	-	-500	mA
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C; pulsed; t_p ≤ 300 μs; δ_{factor} ≤ 0.02	-	300	500	mΩ
TR2: NPN F	Resistor-Equipped Transis	tor (RET)			'	
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		C1 I2 GND
2	B1	base TR1	□6 □5 □4	
3	O2	output (collector) TR2		R1 R2
4	GND	GND (emitter) TR2		TR2
5	12	input (base) TR2	H ₁ H ₂ H ₃	TR1
6	C1	collector TR1	TSSOP6 (SOT363)	E1 B1 O2 aaa-036069

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBLS1501Y		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBLS1501Y	%C1

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
TR1: PNP Io	ow V _{CEsat} transistor		'			
V _{CBO}	collector-base voltage	open emitter		-	-15	V
V_{CEO}	collector-emitter voltage	open base		-	-15	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-500	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse; δ ≤ 0.02		-	-1	Α
I _B	base current			-	-50	mA
I _{BM}	peak base current	$\delta \le 0.02$; single pulse; $t_p \le 1$ ms		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
TR2: NPN R	esistor-Equipped Transistor	(RET)	'		'	
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
V _I	input voltage	input voltage TR2 positive		-	12	V
		input voltage TR2 negative		-	-10	V
Io	output current			-	100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device			'		'	
P _{tot}	total power dissipation			-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
TR1: PNP Io	ow V _{CEsat} transistor					
V _{(BR)CBO}	collector-base breakdown voltage	I_C = -100 μ A; I_E = 0 A; T_{amb} = 25 °C	-15	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-15	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	$I_C = 0 \text{ A}; I_E = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$	-6	-	-	V
Сво	collector-base cut-off	V _{CB} = -15 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -15 V; I _E = 0 A; T _{amb} = 150 °C	-	-	-50	μA
CES	collector-emitter cut-off current	V _{CE} = -15 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
ЕВО	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
n _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -10 mA; pulsed; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	150	-	-	
		V_{CE} = -2 V; I_{C} = -500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	90	-	-	
V _{CEsat} collector-emitter saturation voltage		I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	-	-	-25	mV
	saturation voltage	I_C = -200 mA; I_B = -10 mA; T_{amb} = 25 °C	-	-	-150	mV
		I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02 %; T_{amb} = 25 °C	-	-	-250	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C; pulsed; $t_p \le 300 \ \mu s$;	-	300	500	mΩ
V _{BEsat}	base-emitter saturation voltage	δ _{factor} ≤ 0.02	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C; pulsed; $t_p \le 300$ μs; $\delta_{factor} \le 0.02$	-	-	-0.9	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	10	pF
f⊤	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	280	-	MHz
TR2: NPN R	esistor-Equipped Transist	or (RET)				
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0 A; T _{amb} = 25 °C	50	-	-	V
СВО	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
СЕО	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	1	μA
	current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 150 °C	-	-	50	μA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	2	mA
h _{FE}	DC current gain	V _{CF} = 5 V; I _C = 20 mA; T _{amb} = 25 °C	30	-	-	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	150	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	-	1.2	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	2	1.6	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	-	2.5	pF

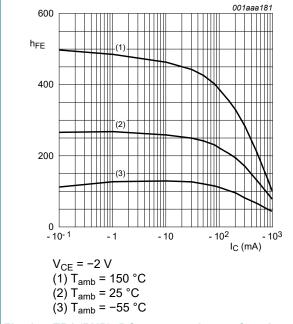


Fig. 1. TR1 (PNP): DC current gain as a function of collector current; typical values

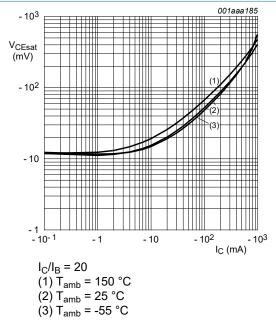


Fig. 2. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

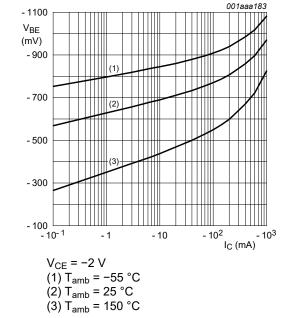


Fig. 3. TR1 (PNP): Base-emitter voltage as a function of collector current; typical values

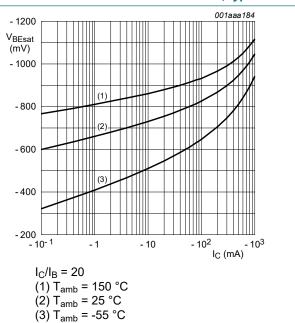
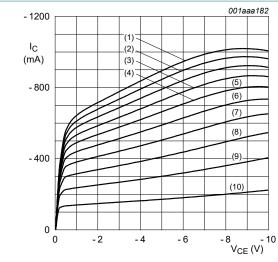


Fig. 4. TR1 (PNP): Base-emitter saturation voltage as a function of collector current; typical values

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 T_{amb} = 25 °C

(1) $I_B = -7.0 \text{ mA}$

 $(2) I_B = -6.3 \text{ mA}$

 $(3) I_B = -5.6 \text{ mA}$

 $(4) I_B = -4.9 \text{ mA}$

 $(5) I_B = -4.2 \text{ mA}$

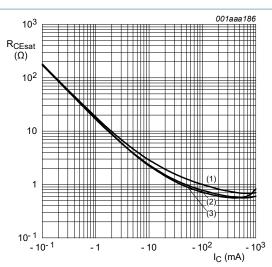
(6) $I_B = -3.5 \text{ mA}$

(7) $I_B = -2.8 \text{ mA}$ (8) $I_B = -2.1 \text{ mA}$

(9) $I_B = -1.4 \text{ mA}$

 $(10) I_B = -0.7 \text{ mA}$

Fig. 5. TR1 (PNP): Collector current as a function of collector-emitter voltage; typical values



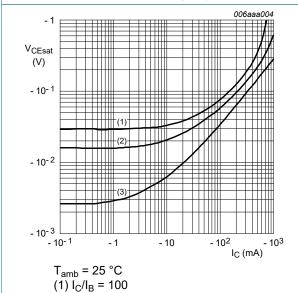
 $I_C/I_B = 20$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb}= 25 °C

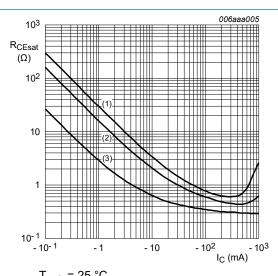
(3) T_{amb} = 150 °C

Fig. 6. TR1 (PNP): Equivalent on-resistance as a function of collector current; typical values



(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

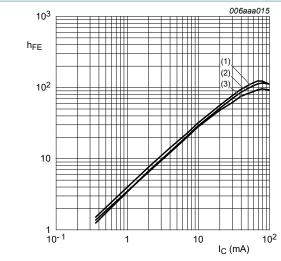
Fig. 7. TR1 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \text{ °C}$ (1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

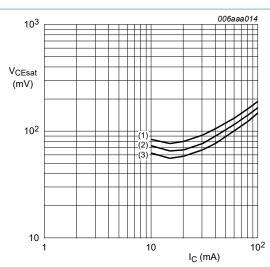
Fig. 8. TR1 (PNP): Equivalent on-resistance as a function of collector current; typical values

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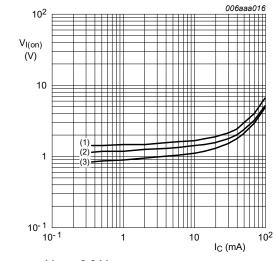
V_{CE} = 5 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

TR2 (NPN): DC current gain as a function of Fig. 9. collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



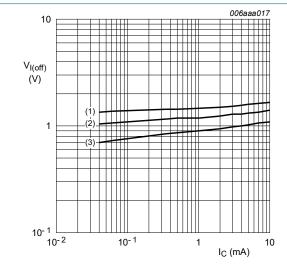
 V_{CE} = 0.3 V

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$





 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

of collector current; typical values

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

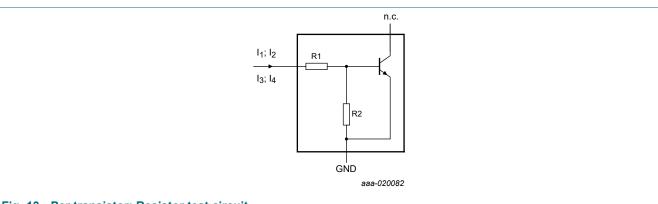


Fig. 13. Per transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

TR2 (NPN)	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I ₁	l ₂	l ₃	14	
PBLS1501Y	2.2	2.2	750 µA	950 μΑ	-750 μA	-950 μA	

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12. Package outline

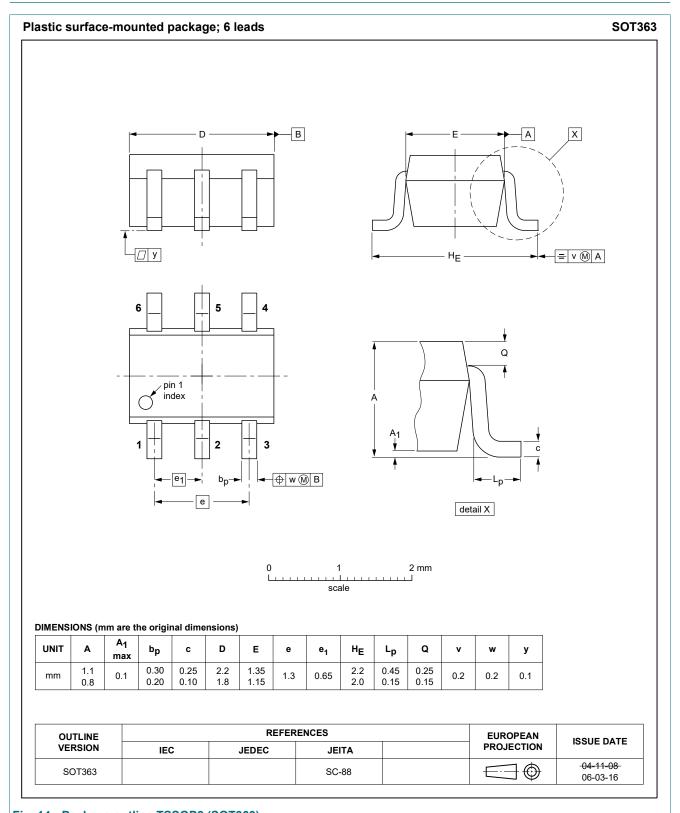
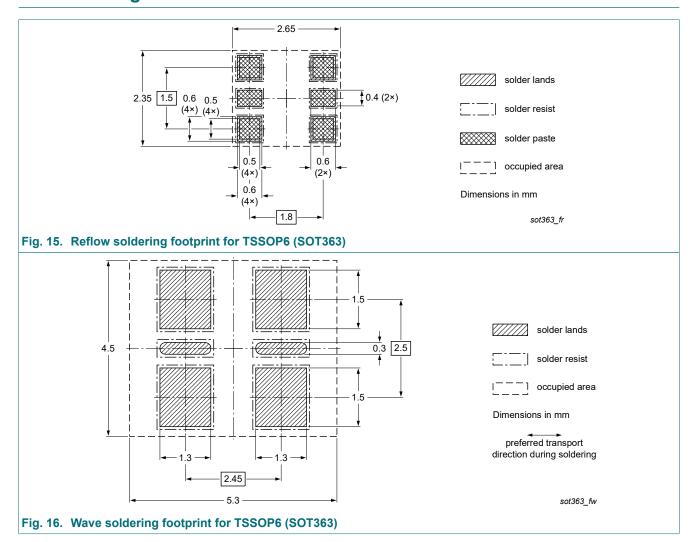


Fig. 14. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBLS1501Y v.4	20230130	Product data sheet	-	PBLS1501Y v.3
Modifications:		stics: collector-emitter cu ation corrected	it-off current	added
PBLS1501Y v.3	20221228	Product data sheet	-	PBLS1501Y_PBLS1501V_2
PBLS1501Y_PBLS1501V_2	20090824	Product data sheet	-	PBLS1501Y_PBLS1501V_1
PBLS1501Y_PBLS1501V_1	20041105	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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